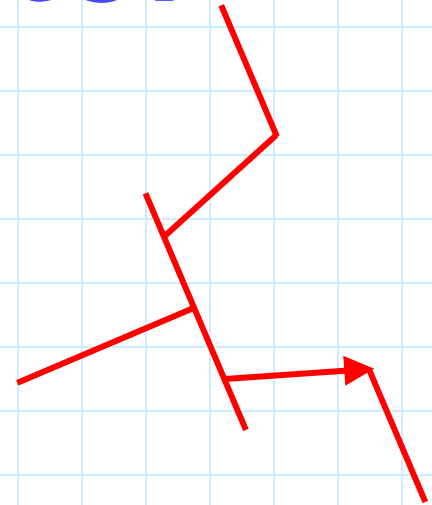


# Chapter I: Basic semiconductor devices



# Objectives (1)

At the end of this chapter, the student should:

- Know and understand the basic operation of semiconductor diodes.
- Know the different models of diodes and how to apply them to the analysis of digital circuits with diodes.
- Know and understand the applications of diodes in digital circuits.
- Know and understand the basic operation and some applications of special-purpose diodes, such as Schottky, LEDs and photodiodes.

# Objectives (2)

At the end of this chapter, the student should:

- Know and understand the basic operation of bipolar junction transistors (BJTs).
- Know and understand the different regions of operation of a BJT.
- Know and understand the operation of a BJT transistor as a switch.
- Apply the knowledge of BJTs to implement basic logic gates.

# Contents

- **1.1 The junction diode.** Foundations
- 1.2 Static regime behaviour
- 1.3 Diode circuits
- 1.4 Special purpose diodes (Schottky, LED, photodiodes)
- **1.5 The bipolar transistor.** Foundations
- 1.6 Output characteristic curves. Load line
- 1.7 Regions of operation
- 1.8 The transistor in switching mode
- 1.9 Transistor-based basic logic gates

# 1.1. Bibliography

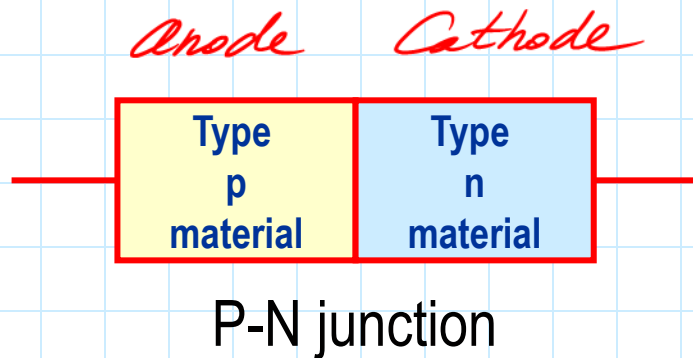
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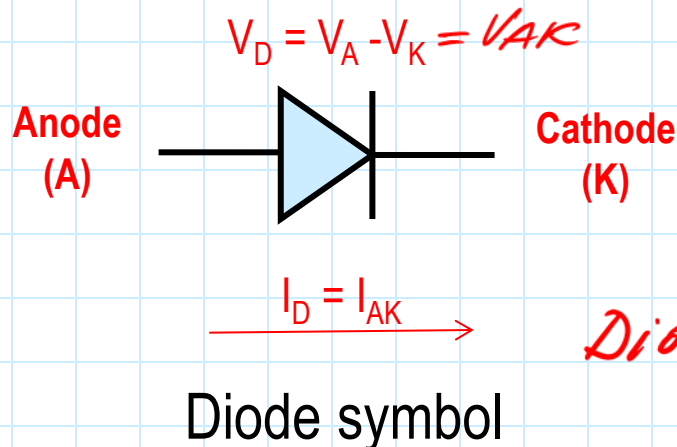
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# 1.1 The junction diode. Foundations



- The P-N junction conducts more easily in forward (from p to n) than in reverse mode.
- The **rectification** concept appears
- Device name: **DIODE**



- Terminals:
  - ◆ **Anode**: type p material
  - ◆ **Cathode**: type n material

*Diodes* {  
- vacuum tubes  
- semiconductor }  
- Discrete  
- Integrated

# 1.1 The junction diode. Foundations

$\eta \rightarrow$  Quality factor ( $\approx 1$ )

- The Diode is a **NON-LINEAR** device

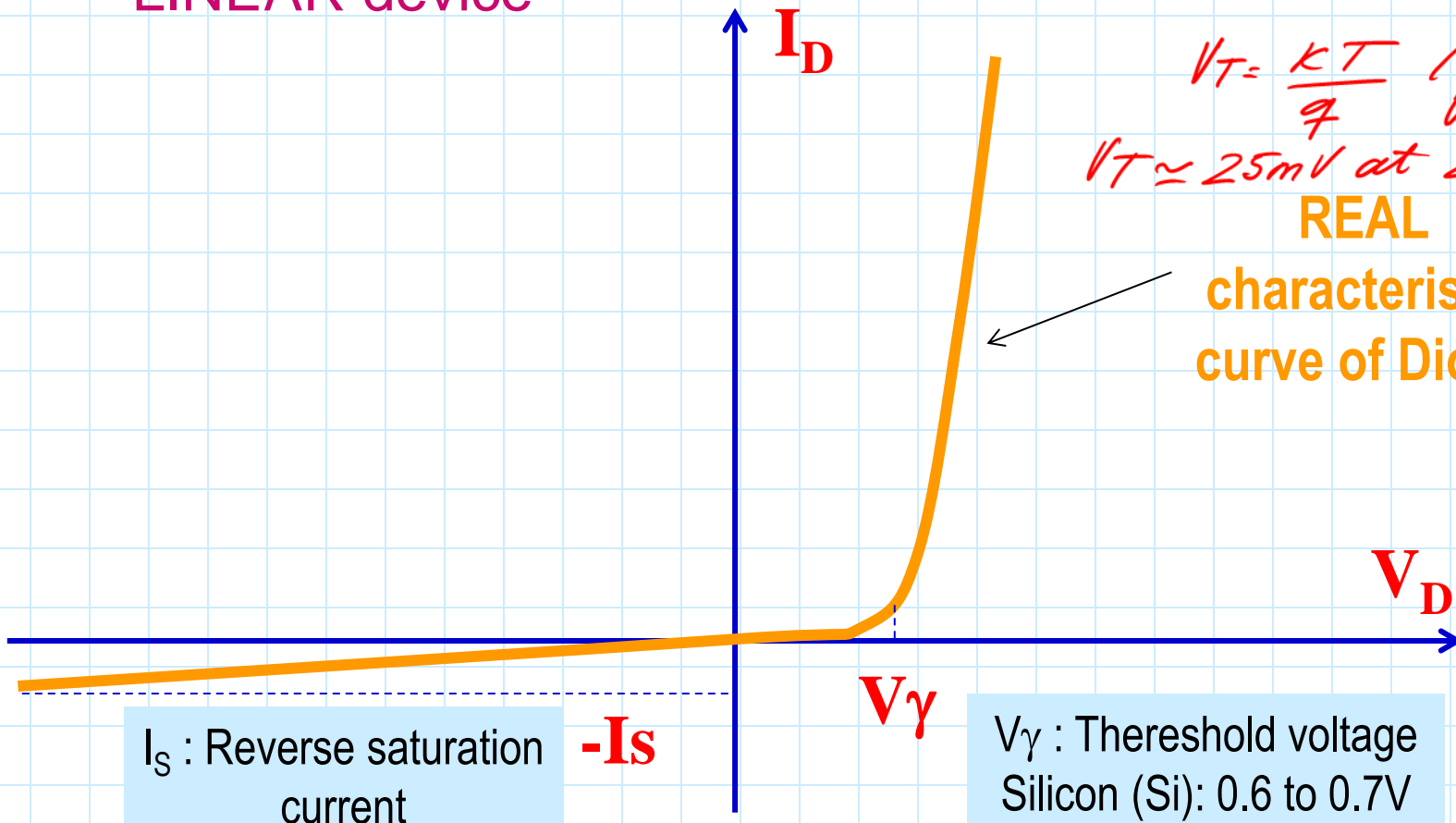
$$I_D = I_S (e^{\frac{V_D}{\eta V_T}} - 1)$$

$V_T = \frac{kT}{q}$  (Thermal Voltage)

$V_T \approx 25\text{mV}$  at  $25^\circ\text{C}$

**REAL**

characteristic  
curve of Diode



$I_S$  : Reverse saturation  
current

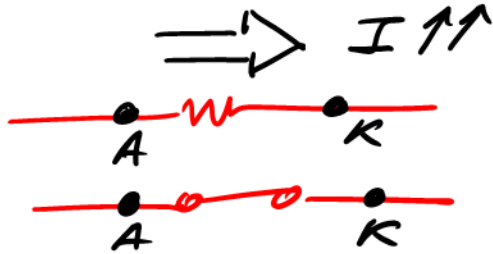
$-I_S$

$V_\gamma$

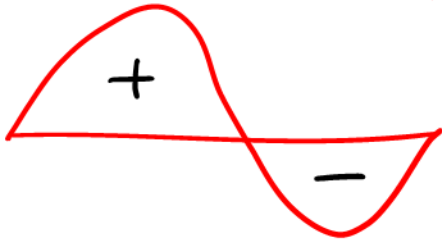
$V_\gamma$  : Threshold voltage  
Silicon (Si): 0.6 to 0.7V

## Forward bias (ON)

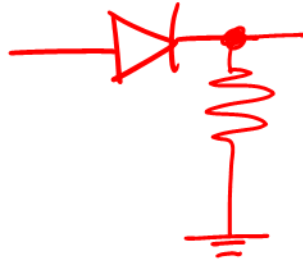
$$V_{AK} > V_\gamma \Rightarrow R_{on} \downarrow \downarrow \downarrow$$



AC



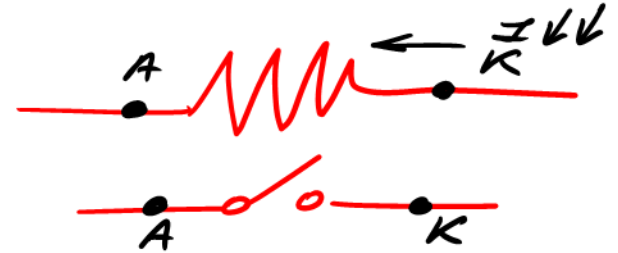
## Rectification



AC  $\longrightarrow$  DC

## Reverse bias (OFF)

$$V_{AK} \leq V_\gamma \Rightarrow R_{on} \uparrow \uparrow \uparrow$$



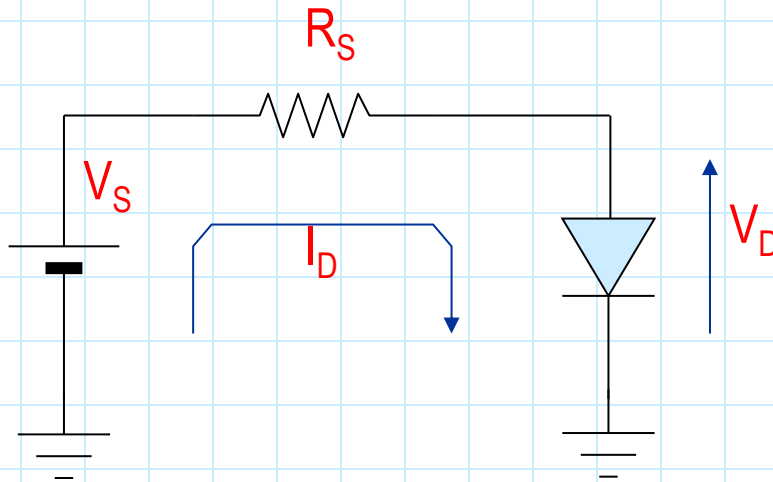
DC





## 1.2 Load line

When we connect the diode with a voltage generator ( $V_S$ ) and a series resistor ( $R_S$ ), these devices bias the diode, putting it in an operating point.



$$I_D = f(V_D)$$

Applying the 2<sup>nd</sup> Kirchhoff law:

$$V_S - I_D R_S - V_D = 0$$

$$I_D = \frac{V_S}{R_S} - \frac{V_D}{R_S}$$

# 1.2 Load line

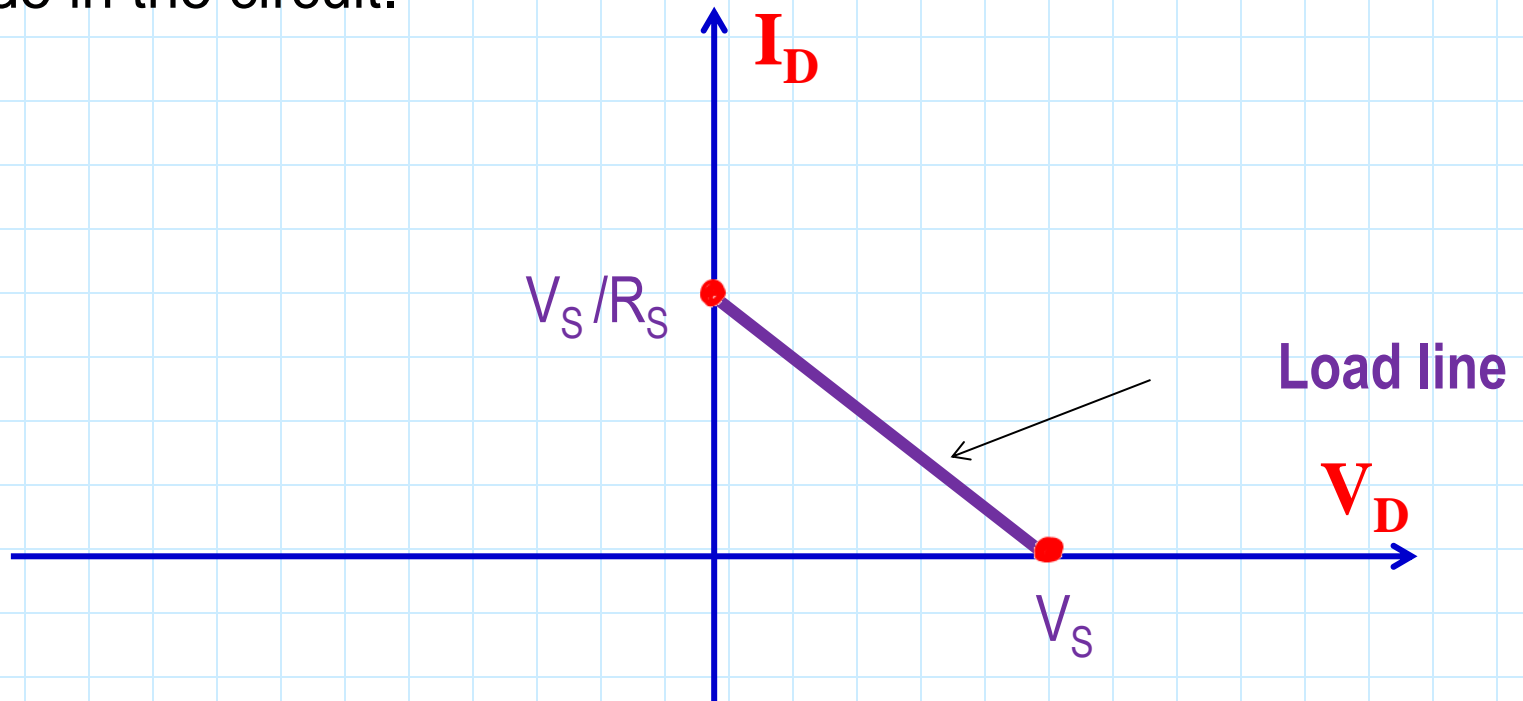
$$I_D = \frac{V_S}{R_S} - \frac{V_D}{R_S}$$

Cross points with the X( $V_D$ ) and Y ( $I_D$ ) axes:

$$\text{When } I_D = 0 \rightarrow V_D = V_S$$

$$\text{When } V_D = 0 \rightarrow I_D = V_S / R_S$$

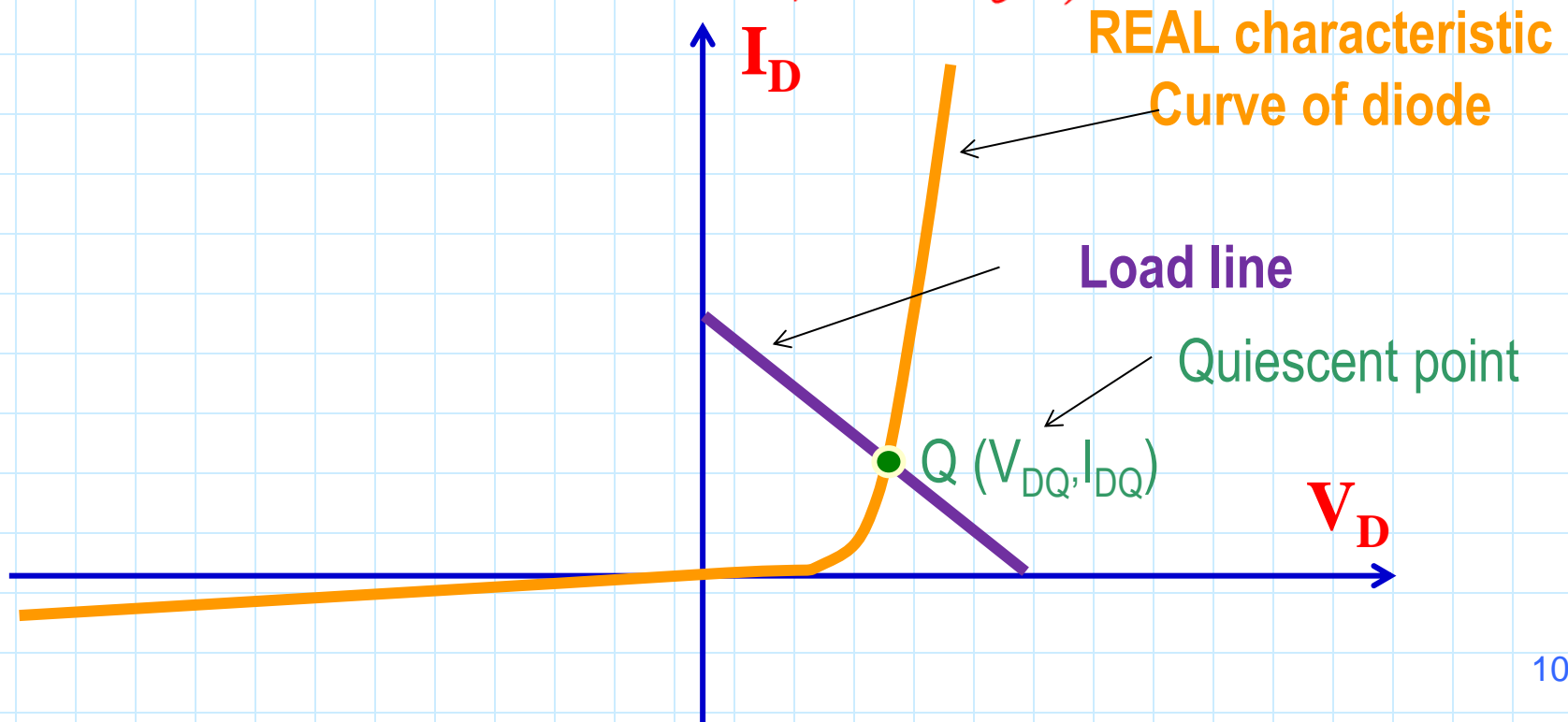
The **LOAD LINE** depends only of elements added to the diode in the circuit.



# 1.2 Quiescent point

- The diode has to meet its **CHARACTERISTIC CURVE**
- The intersection point of the real characteristic curve of diode and the load line defines the **QUIESCENT POINT** of diode

*↳ Operating point*

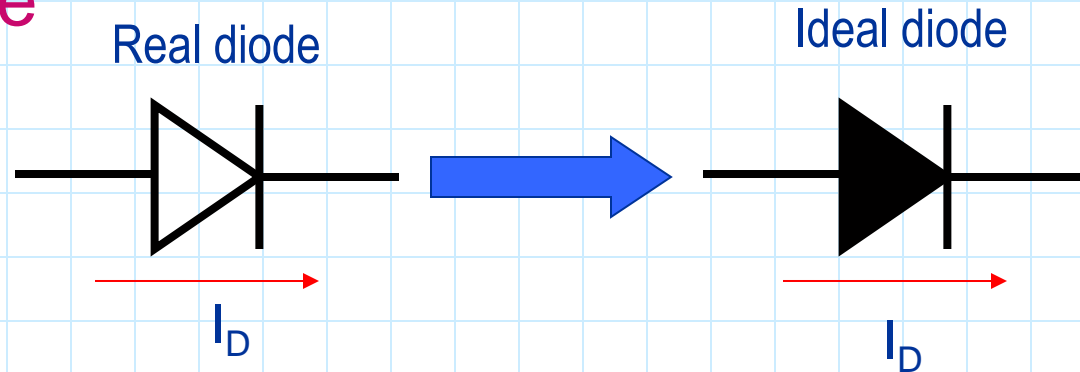


# 1.2 Diode approximations and models

- We can define diode MODELS that approximate its behaviour with an increasing accuracy:
  1. Ideal model
  2. Ideal model with threshold voltage.
  3. ...

# 1.2 Diode models (1)

## 1. Ideal diode



The behaviour is similar to a switch:

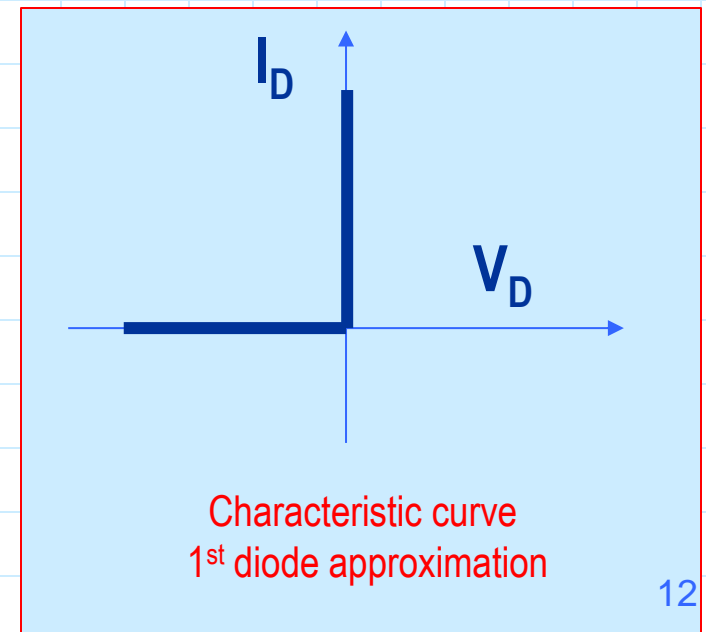
- ◆ Direct bias: closed (ON)

☞  $V_D = 0$  for all  $I_D > 0$



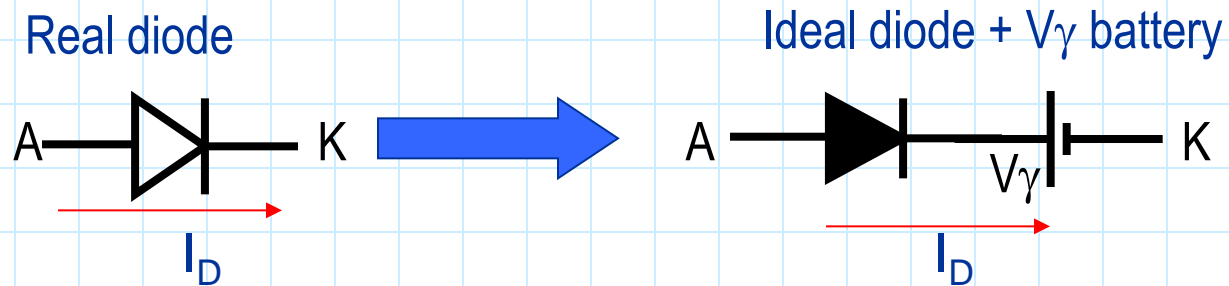
- ◆ Reverse bias: open (OFF)

☞  $I_D = 0$  for all  $V_D < 0$

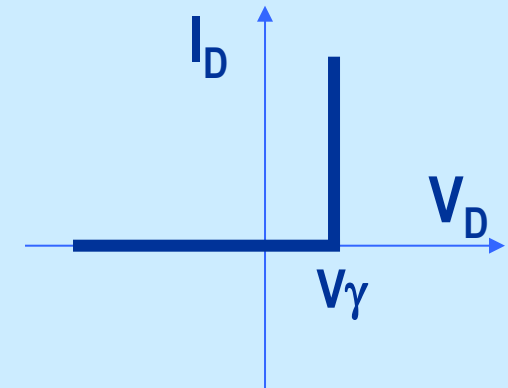


# 1.2 Diode models (2)

## 2. Ideal diode with threshold voltage $V_\gamma$

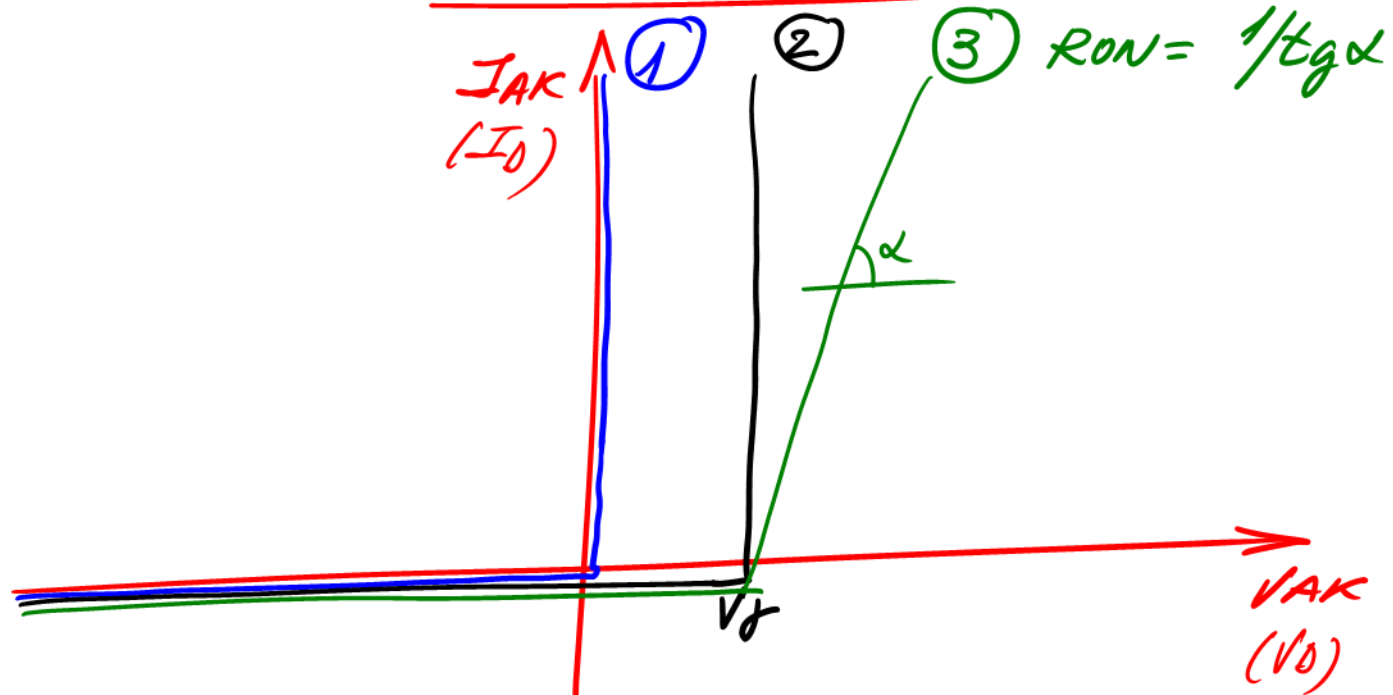


$V_D = V_\gamma$  for all  $I_D > 0$



Characteristic curve  
2<sup>nd</sup> diode approximation

## More models



Models ① and ② enough for digital applications